

Features

- Low On-Resistance
 - 11mΩ @ $V_{GS} = -10V$
 - 17mΩ @ $V_{GS} = -4.5V$
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- **Lead Free By Design/RoHS Compliant (Note 2)**
- **"Green" Device (Note 4)**
- **Qualified to AEC-Q101 Standards for High Reliability**

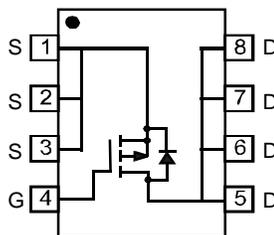
Mechanical Data

- Case: SO-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020D
- Terminals Connections: See Diagram
- Terminals: Finish - Matte Tin annealed over Copper lead frame. Solderable per MIL-STD-202, Method 208
- Marking Information: See Page 4
- Ordering Information: See Page 4
- Weight: 0.072g (approximate)



TOP VIEW

SO-8


 TOP VIEW
Internal Schematic

Maximum Ratings @ $T_A = 25^\circ C$ unless otherwise specified

Characteristic			Symbol	Value	Units
Drain-Source Voltage			V_{DSS}	-30	V
Gate-Source Voltage			V_{GSS}	± 20	V
Drain Current (Note 1)	Steady State	$T_A = 25^\circ C$	I_D	-13	A
		$T_A = 70^\circ C$		-9.75	A
Pulsed Drain Current (Note 3)			I_{DM}	-45	A

Thermal Characteristics

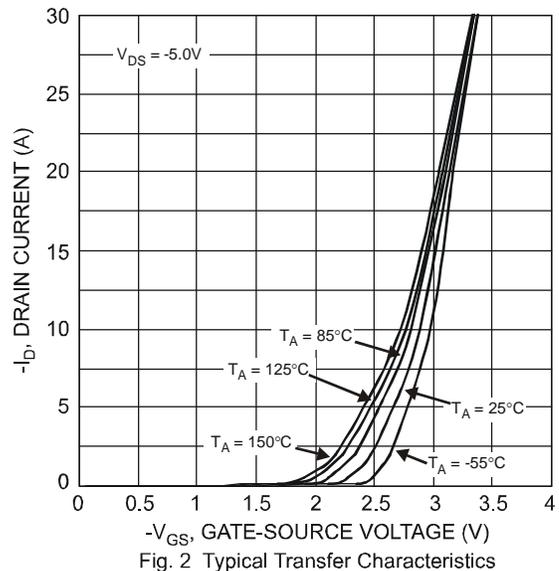
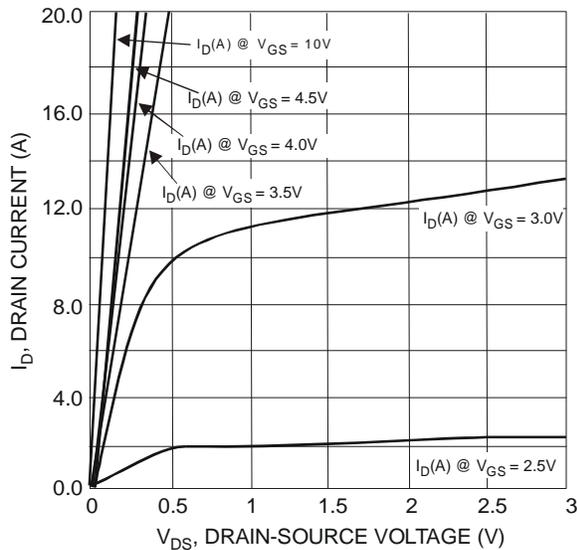
Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 1)	P_D	2.5	W
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	50	$^\circ C/W$
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to +150	$^\circ C$

- Notes:
1. Device mounted on 2 oz. Copper pads on FR-4 PCB with $R_{\theta JA} = 50^\circ C/W$.
 2. No purposefully added lead.
 3. Pulse width $\leq 10\mu S$, Duty Cycle $\leq 1\%$.
 4. Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead_free/index.php.

Electrical Characteristics @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 5)						
Drain-Source Breakdown Voltage	BV _{DSS}	-30	—	—	V	V _{GS} = 0V, I _D = -250μA
Zero Gate Voltage Drain Current	I _{DSS}	—	—	-1	μA	V _{DS} = -30V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	—	—	±100	nA	V _{GS} = ±20V, V _{DS} = 0V
ON CHARACTERISTICS (Note 5)						
Gate Threshold Voltage	V _{GS(th)}	-1	—	-2	V	V _{DS} = V _{GS} , I _D = -250μA
Static Drain-Source On-Resistance	R _{DS(ON)}	—	9 14	11 17	mΩ	V _{GS} = -10V, I _D = -13A V _{GS} = -4.5V, I _D = -10A
Forward Transconductance	g _{fs}	—	15	—	S	V _{DS} = -15V, I _D = -8A
Diode Forward Voltage (Note 5)	V _{SD}	-0.5	—	-1.1	V	V _{GS} = 0V, I _S = -2.1A
DYNAMIC CHARACTERISTICS						
Input Capacitance	C _{iss}	—	2748	—	pF	V _{DS} = -20V, V _{GS} = 0V f = 1.0MHz
Output Capacitance	C _{oss}	—	357	—	pF	
Reverse Transfer Capacitance	C _{rss}	—	356	—	pF	
Gate Resistance	R _G	—	2.0	—	Ω	V _{DS} = 0V, V _{GS} = 0V f = 1.0MHz
SWITCHING CHARACTERISTICS						
Total Gate Charge	Q _g	—	30.0 60.4	—	nC	V _{DS} = -10V, V _{GS} = -4.5V, I _D = -13A V _{DS} = -10V, V _{GS} = -10V, I _D = -13A
Gate-Source Charge	Q _{gs}	—	7.2	—		V _{DS} = -10V, V _{GS} = -10V, I _D = -13A
Gate-Drain Charge	Q _{gd}	—	16.4	—		V _{DS} = -10V, V _{GS} = -10V, I _D = -13A
Turn-On Delay Time	t _{d(on)}	—	11.2	—	ns	V _{DS} = -15V, V _{GS} = -10V, I _D = -1A, R _G = 6.0Ω
Rise Time	t _r	—	12.4	—		
Turn-Off Delay Time	t _{d(off)}	—	104.9	—		
Fall Time	t _f	—	61.7	—		

Notes: 5. Short duration pulse test used to minimize self-heating effect.



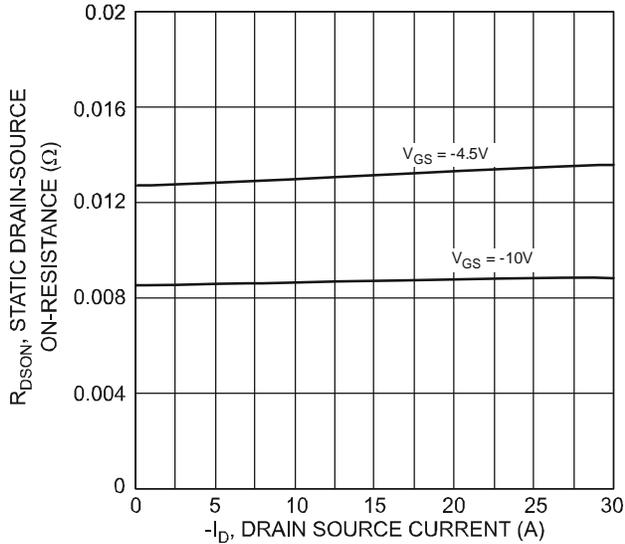


Fig. 3 On-Resistance vs. Drain Current & Gate Voltage

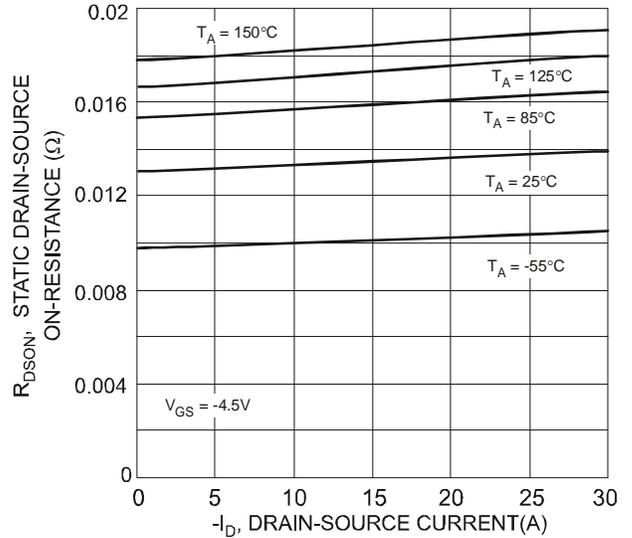


Fig. 4 On-Resistance vs. Drain Current & Gate Voltage

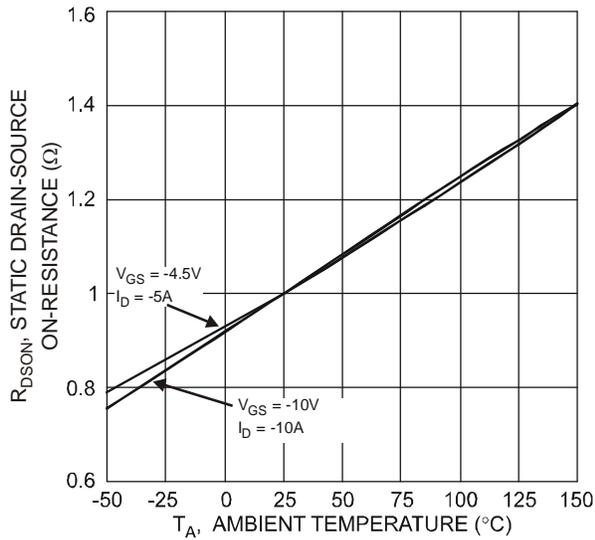


Fig. 5 Static Drain-Source On-Resistance vs. Ambient Temperature

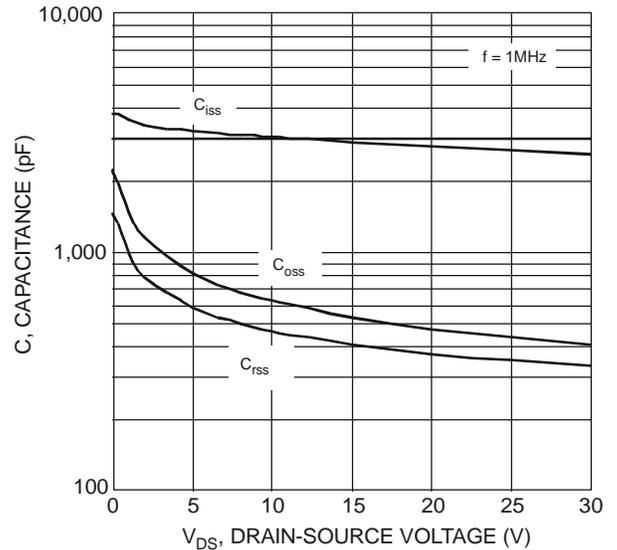


Fig. 6 Typical Total Capacitance

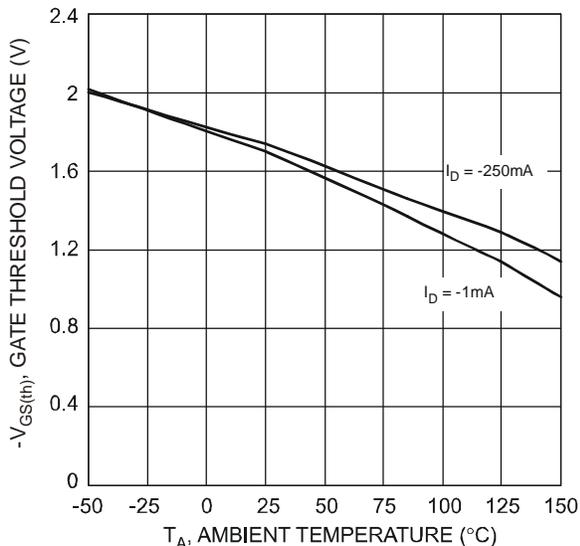


Fig. 7 Gate Threshold Variation vs. Ambient Temperature

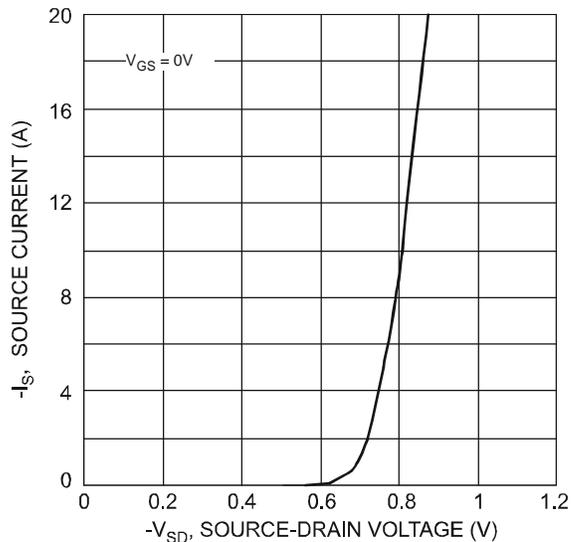


Fig. 8 Forward Drain Current vs. Source-Drain Voltage

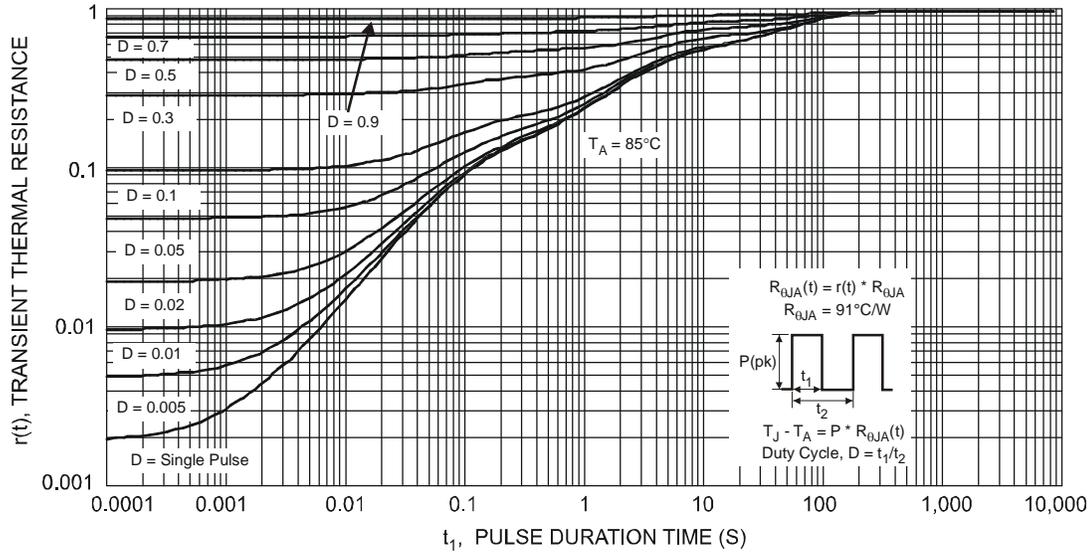


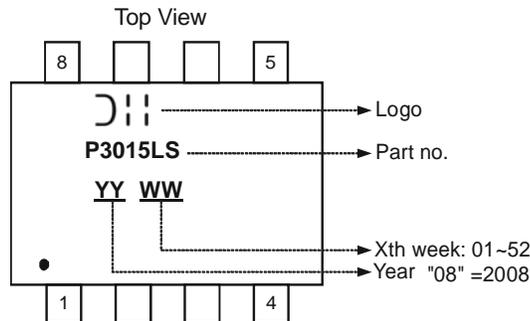
Fig. 9 Transient Thermal Resistance

Ordering Information (Note 6)

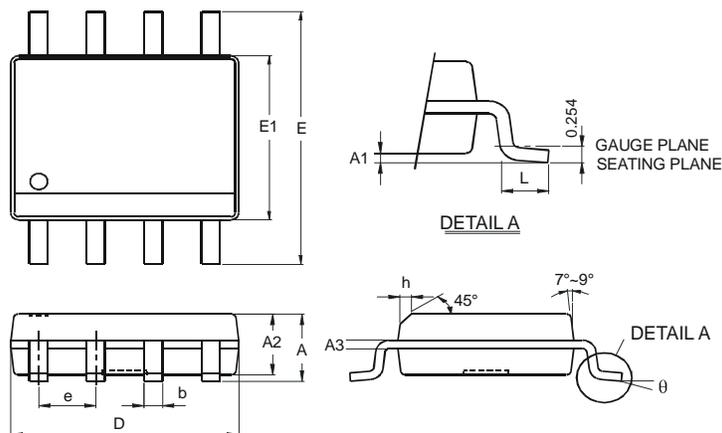
Part Number	Case	Packaging
DMP3015LSS-13	SO-8	2500/Tape & Reel

Notes: 6. For packaging details, go to our website at <http://www.diodes.com/datasheets/ap02007.pdf>.

Marking Information

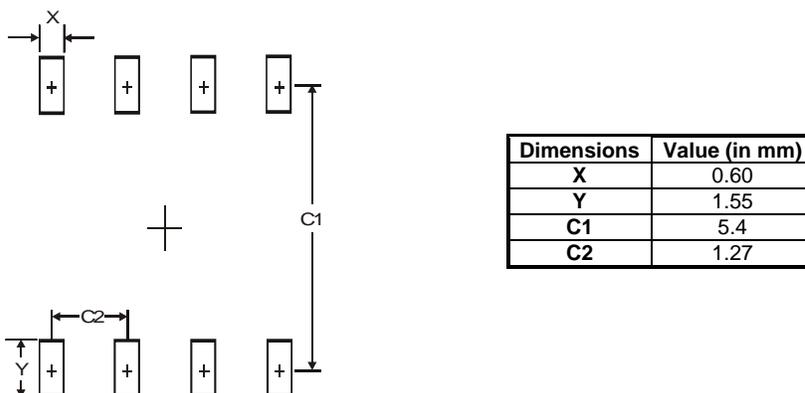


Package Outline Dimensions



SO-8		
Dim	Min	Max
A	—	1.75
A1	0.08	0.25
A2	1.30	1.50
A3	0.20 Typ.	
b	0.3	0.5
D	4.80	5.30
E	5.79	6.20
E1	3.70	4.10
e	1.27 Typ.	
h	—	0.35
L	0.38	1.27
θ	0°	8°
All Dimensions in mm		

Suggested Pad Layout



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Офис по работе с юридическими лицами:

105318, г.Москва, ул.Щербаковская д.3, офис 1107, 1118, ДЦ «Щербаковский»

Телефон: +7 495 668-12-70 (многоканальный)

Факс: +7 495 668-12-70 (доб.304)

E-mail: info@moschip.ru

Skype отдела продаж:

moschip.ru

moschip.ru_4

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moschip.ru_9